

## Features

- 600 V, 20 A, Low Collector-Emitter Saturation Voltage ( $V_{CE(sat)}$ )
- Trench-Gate Field-Stop technology
- Optimized for conduction
- Low switching loss
- RoHS compliant\*

## Applications

- Switch-Mode Power Supplies (SMPS)
- Uninterruptible Power Sources (UPS)
- Power Factor Correction (PFC)
- Stepper motors

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## BIDW20N60T Insulated Gate Bipolar Transistor (IGBT)

### General Information

The Bourns® Model BIDW20N60T IGBT device combines technology from a MOS gate and a bipolar transistor for an optimum component for high voltage and high current applications. This device uses Trench-Gate Field-Stop technology providing greater control of dynamic characteristics with a lower conduction loss and fewer switching losses. In addition, this structure provides a positive temperature coefficient.

### Additional Information

Click these links for more information:



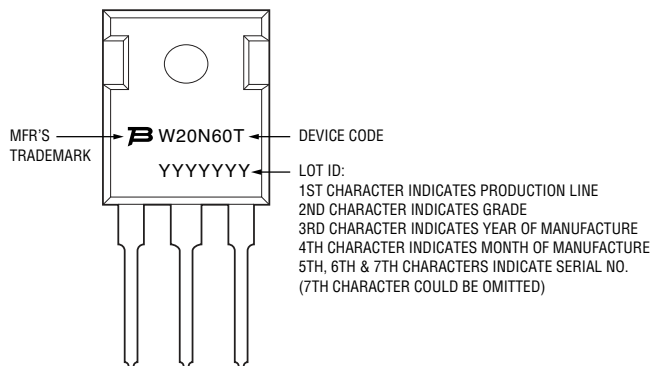
### Maximum Electrical Ratings ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CES}$	600	V
Continuous Collector Current ( $T_C = 25\text{ }^\circ\text{C}$ ), limited by $T_{jmax}$	$I_C$	40	A
Continuous Collector Current ( $T_C = 100\text{ }^\circ\text{C}$ ), limited by $T_{jmax}$	$I_C$	20	A
Pulsed Collector Current, $t_p$ limited by $T_{jmax}$	$I_{CP}$	60	A
Gate-Emitter Voltage	$V_{GE}$	$\pm 20$	V
Continuous Forward Current ( $T_C = 25\text{ }^\circ\text{C}$ ), limited by $T_{jmax}$	$I_F$	40	A
Continuous Forward Current ( $T_C = 100\text{ }^\circ\text{C}$ ), limited by $T_{jmax}$	$I_F$	20	A
Short-circuit Withstand Time ( $V_{CE} = 300\text{ V}$ , $V_{GE} = 15\text{ V}$ )	$T_{SC}$	10	$\mu\text{s}$
Total Power Dissipation	$P_{total}$	192	W
Storage Temperature	$T_{STG}$	-55 to +150	$^\circ\text{C}$
Operating Junction Temperature	$T_j$	-55 to +150	$^\circ\text{C}$

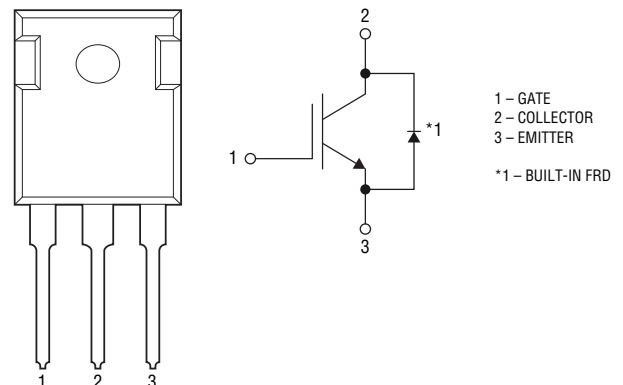
### Thermal Resistance

Parameter	Symbol	Max	Unit
IGBT Thermal Resistance Junction - Case	$R_{th(j-c)}_{IGBT}$	0.65	$^\circ\text{C/W}$
Diode Thermal Resistance Junction - Case	$R_{th(j-c)}_{Diode}$	1.19	$^\circ\text{C/W}$

### Typical Part Marking



### Internal Circuit



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# BIDW20N60T Insulated Gate Bipolar Transistor (IGBT)

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## Static Electrical Characteristics ( $T_C = 25\text{ }^\circ\text{C}$ , Unless Otherwise Specified)

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Collector-Emitter Breakdown Voltage	$BV_{CES}$	$V_{GE} = 0\text{ V}, I_C = 250\text{ }\mu\text{A}$	600	—	—	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE} = 15\text{ V}, I_C = 20\text{ A}$ $T_C = 25\text{ }^\circ\text{C}$	—	1.7	2.4	V
		$V_{GE} = 15\text{ V}, I_C = 20\text{ A}$ $T_C = 125\text{ }^\circ\text{C}$	—	1.9	—	
Diode Forward On-Voltage	$V_F$	$I_F = 20\text{ A}, T_C = 25\text{ }^\circ\text{C}$	—	1.8	—	V
		$I_F = 20\text{ A}, T_C = 125\text{ }^\circ\text{C}$	—	1.5	—	V
Gate Threshold Voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}, I_C = 250\text{ }\mu\text{A}$	4.0	5.0	6.5	V
Collector Cut-off Current	$I_{CES}$	$V_{GE} = 0\text{ V}, V_{CE} = 600\text{ V}$	—	—	200	$\mu\text{A}$
Gate-Emitter Leakage Current	$I_{GES}$	$V_{CE} = 0\text{ V}, V_{GE} = \pm 20\text{ V}$	—	—	$\pm 400$	nA

## Dynamic Electrical Characteristics ( $T_C = 25\text{ }^\circ\text{C}$ , Unless Otherwise Specified)

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Input Capacitance	$C_{ies}$	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V},$ $f = 1\text{ MHz}$	—	1100	—	pF
Output Capacitance	$C_{oes}$		—	55	—	
Reverse Transfer Capacitance	$C_{res}$		—	22	—	
Total Gate Charge	$Q_g$	$V_{CE} = 400\text{ V}, V_{GE} = 15\text{ V}$ $I_C = 20.0\text{ A}$	—	52	—	nC
Gate-Emitter Charge	$Q_{ge}$		—	15	—	
Gate-Collector Charge	$Q_{gc}$		—	22	—	

## IGBT Switching Characteristics (Inductive Load, $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise specified)

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Turn-on Delay Time	$t_{d(on)}$	$V_{CE} = 400\text{ V}, V_{GE} = 15\text{ V}$ $I_C = 20.0\text{ A}, R_G = 10\text{ }\Omega$	—	19	—	ns
Current Rise Time	$t_r$		—	55	—	ns
Turn-off Delay Time	$t_{d(off)}$		—	48	—	ns
Current Fall Time	$t_f$		—	115	—	ns
Turn-on Switching Energy	$E_{on}$		—	1	—	mJ
Turn-off Switching Energy	$E_{off}$		—	0.3	—	mJ
Total Switching Energy	$E_{ts}$		—	1.3	—	mJ

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# BIDW20N60T Insulated Gate Bipolar Transistor (IGBT)

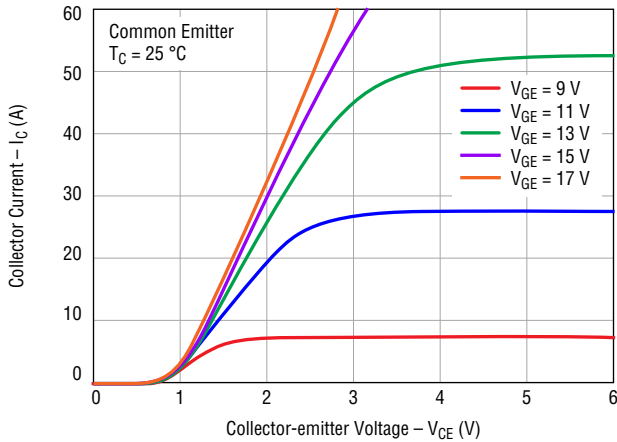
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## Diode Switching Characteristics ( $T_C = 25\text{ °C}$ , unless otherwise specified)

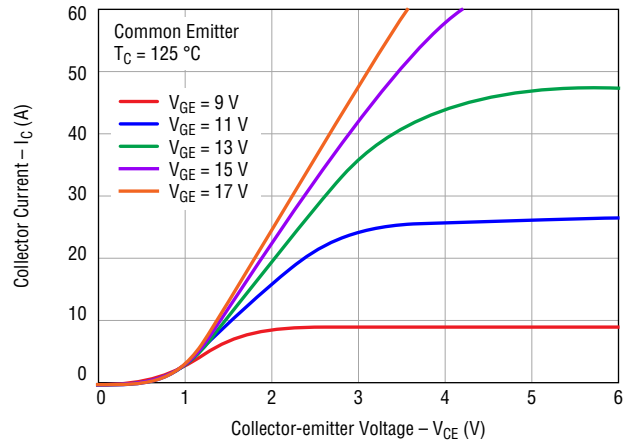
Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Reverse Recovery Time	$t_{rr}$	$di_F/dt = 200\text{ A}/\mu\text{s}$ $I_F = 20.0\text{ A}$	—	33.7	—	ns
Reverse Recovery Charge	$Q_{rr}$		—	73.3	—	nC

## Electrical Characteristic Performance

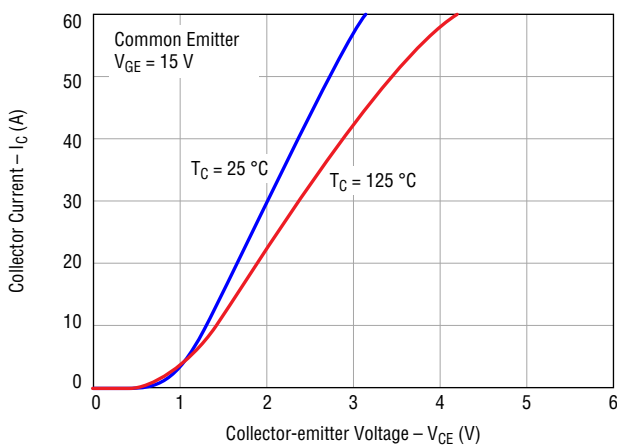
### Typical Output Characteristics



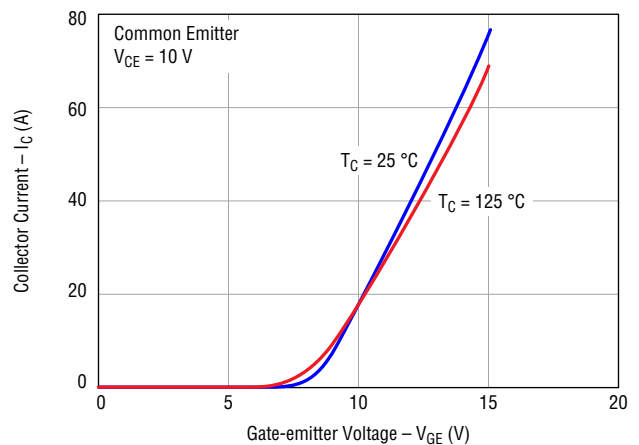
### Typical Output Characteristics



### Typical Saturation Voltage Characteristics



### Typical Transfer Characteristics



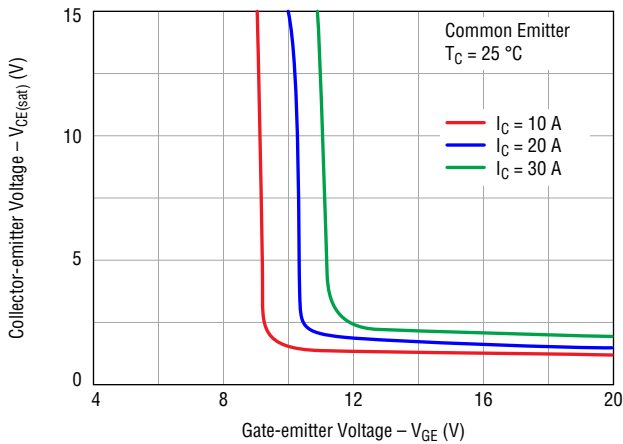
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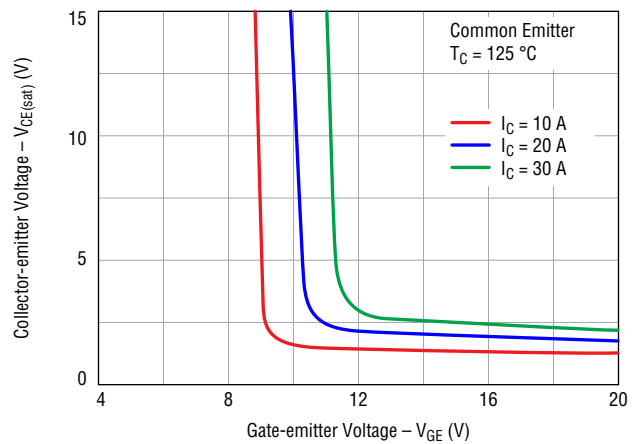
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**Electrical Characteristic Performance (continued)**

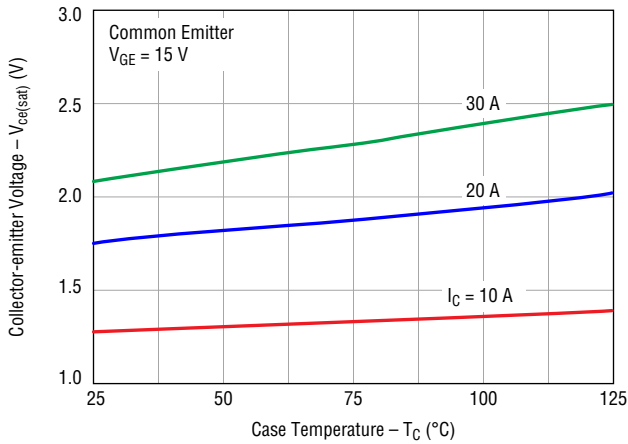
**Typical  $V_{CE(sat)}$  vs  $V_{GE}$  @  $T_C = 25^\circ\text{C}$**



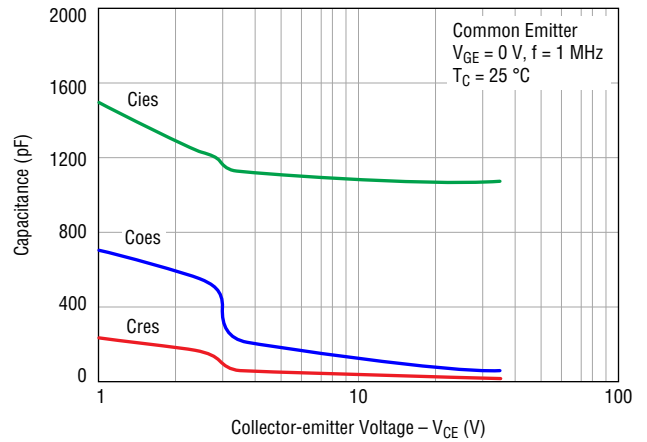
**Typical  $V_{CE(sat)}$  vs  $V_{GE}$  @  $T_C = 125^\circ\text{C}$**



**Typical  $V_{CE(sat)}$  vs Case Temperature**



**Typical Capacitance Characteristics**



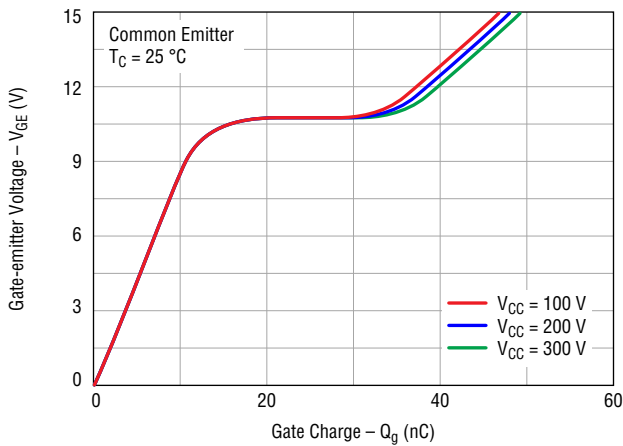
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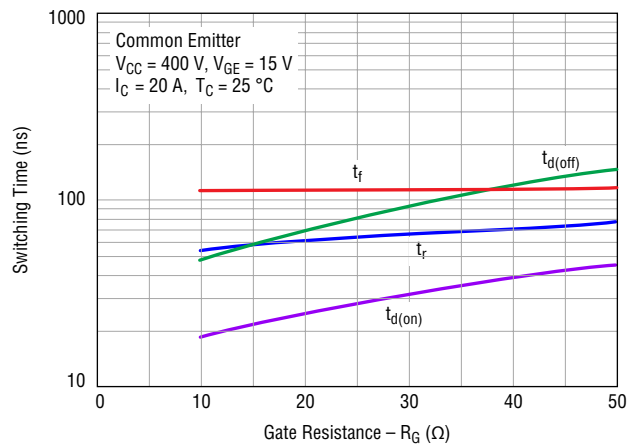
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Electrical Characteristic Performance (continued)

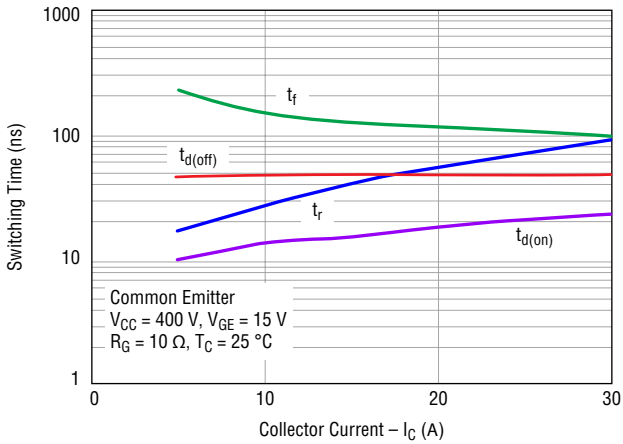
Typical Gate Charge Characteristics



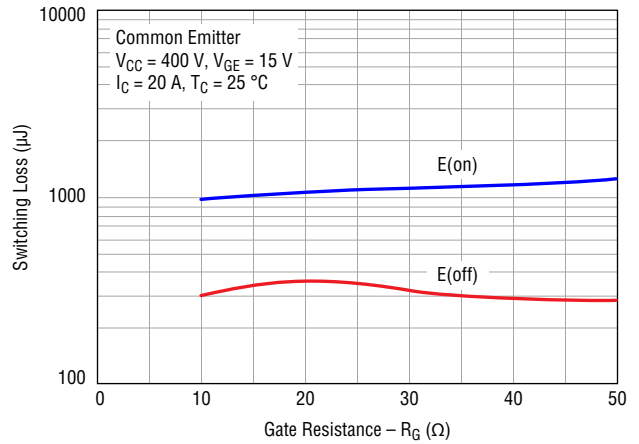
Typical Switching Time Characteristics vs  $R_G$



Typical Switching Time Characteristics vs  $I_C$



Typical Switching Loss vs  $R_G$



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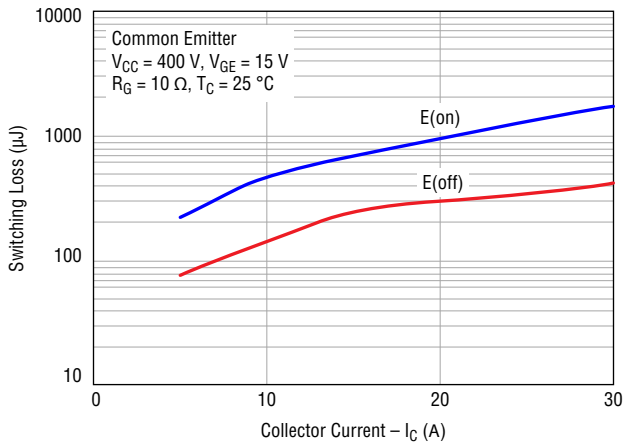
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# BIDW20N60T Insulated Gate Bipolar Transistor (IGBT)

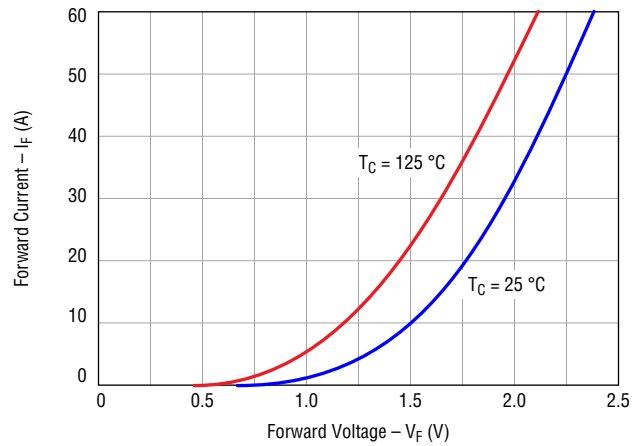
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## Electrical Characteristic Performance (continued)

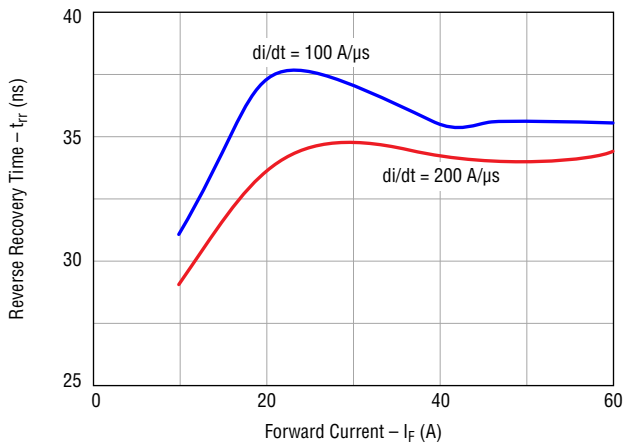
### Typical Switching Loss Characteristics vs $I_C$



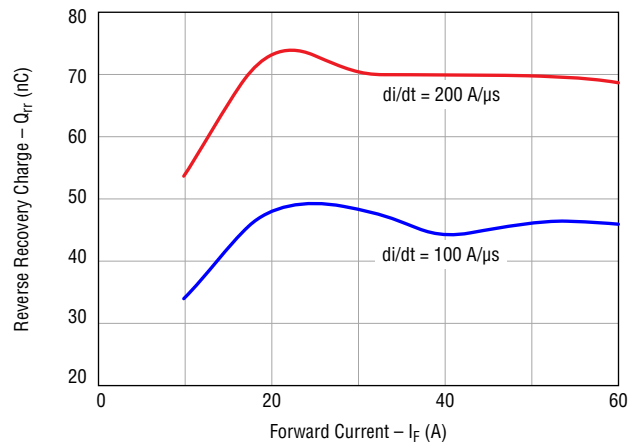
### Typical Diode $I_F$ vs $V_F$



### Typical Reverse Recovery Time vs $I_F$



### Typical Reverse Recovery Charge vs $I_F$



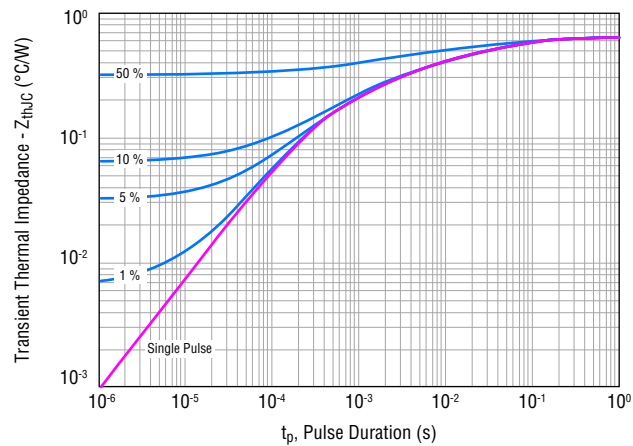
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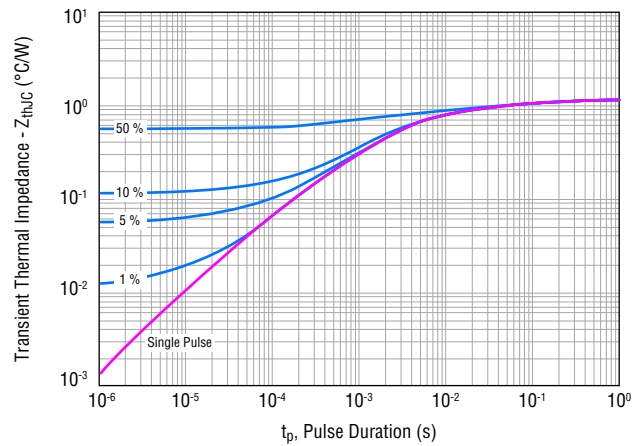
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Electrical Characteristic Performance (continued)

IGBT Transient Thermal Impedance vs  $t_{p(on)}$  Duration ( $D=t_p/T$ )



Diode Transient Thermal Impedance vs  $t_{p(on)}$  Duration ( $D=t_p/T$ )



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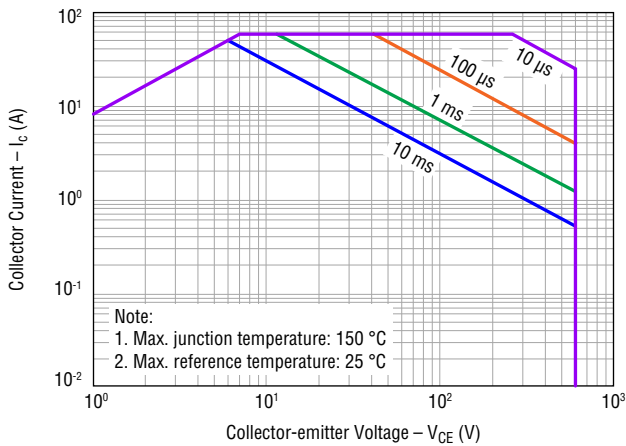
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# BIDW20N60T Insulated Gate Bipolar Transistor (IGBT)



## Electrical Characteristic Performance (continued)

### Forward Bias Safe Operating Area

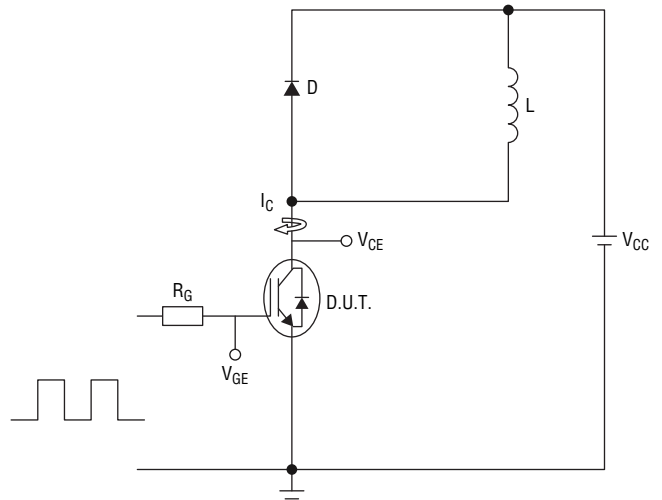


### How to Order

**B I D W 20 N 60 T**

- B = Bourns®
- I = IGBT
- Type
  - D = Discrete
- Package Code
  - W = TO-247
- Current Rating
  - 20 = 20 A
- Device Type
  - N = N-channel
- Nominal Voltage (divided by 10)
  - 60 = 600 V
- Optimization
  - T = Medium Speed

## Inductive Load Test Circuit



$L = 2.8 \text{ mH}$ ,  $V_{CE} = 400 \text{ V}$ ,  $V_{GE} = 15 \text{ V}$ ,  $I_C = 20 \text{ A}$ ,  $R_G = 10 \Omega$

## Environmental Characteristics

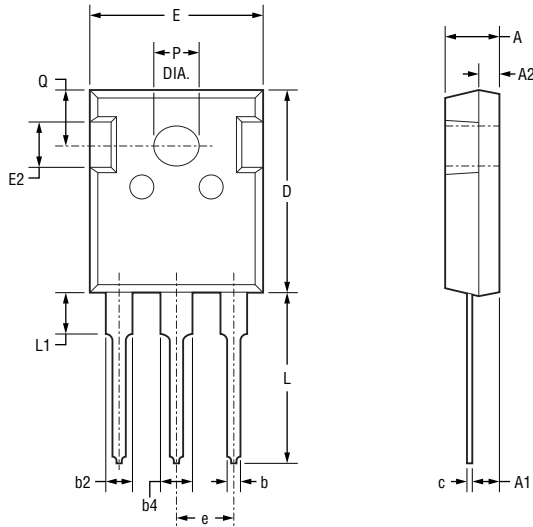
ESD Class (HBM)..... 1C



# BIDW20N60T Insulated Gate Bipolar Transistor (IGBT)

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## Product Dimensions



DIMENSIONS:  $\frac{\text{MM}}{\text{(INCHES)}}$

Symbol	Min.	Nom.	Max.
A	$\frac{4.80}{(.189)}$	$\frac{5.00}{(.197)}$	$\frac{5.20}{(.205)}$
A1	$\frac{2.21}{(.087)}$	$\frac{2.41}{(.095)}$	$\frac{2.59}{(.102)}$
A2	$\frac{1.85}{(.073)}$	$\frac{2.00}{(.079)}$	$\frac{2.15}{(.085)}$
b	$\frac{1.11}{(.044)}$	—	$\frac{1.36}{(.054)}$
b2	$\frac{1.91}{(.075)}$	—	$\frac{2.25}{(.089)}$
b4	$\frac{2.91}{(.115)}$	—	$\frac{3.25}{(.128)}$
c	$\frac{0.51}{(.020)}$	—	$\frac{0.75}{(.030)}$
D	$\frac{20.80}{(.819)}$	$\frac{21.00}{(.827)}$	$\frac{21.30}{(.839)}$
E	$\frac{15.50}{(.610)}$	$\frac{15.80}{(.622)}$	$\frac{16.10}{(.634)}$
E2	$\frac{4.40}{(.173)}$	$\frac{5.00}{(.197)}$	$\frac{5.20}{(.205)}$
e	$\frac{5.44}{(.214)} \text{ BSC}$		
L	$\frac{19.72}{(.776)}$	$\frac{19.92}{(.784)}$	$\frac{20.22}{(.796)}$
L1	—	—	$\frac{4.30}{(.169)}$
P	$\frac{3.40}{(.134)}$	—	$\frac{3.80}{(.150)}$
Q	$\frac{5.60}{(.220)}$	$\frac{5.80}{(.228)}$	$\frac{6.00}{(.236)}$

## Packaging Specifications

BIDW20N60T ..... 30 pieces per tube

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